

Form PTO 1449
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192520US2SERIAL NO. 09/594,479
New Application

LIST OF REFERENCES CITED BY APPLICANT

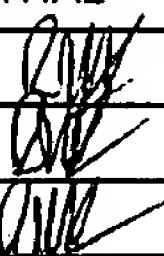
APPLICANT

Hayashi OTSUKI, et al.


FILING DATE 6/14/2000
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GROUP 2877

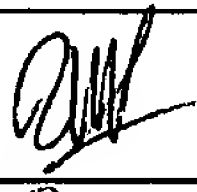

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	5,271,264	12/21/93	Steve G. Chanayem	—	—	
	AB	5,347,138	09/13/94	Derek G. Aqui, et al.	—	—	
	AC	5,438,526	08/01/95	Satoshi Itoh, et al.	—	—	
	AD						
	AE						
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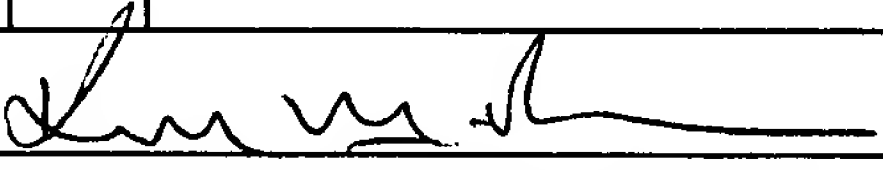
FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO	
	AO	6-110870	04/22/94	Japan (with English Abstract)		x
	AP	10-242060	09/11/98	Japan (with English Abstract)		x
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	Tom WINTER, et al., "ISPM CHARACTERIZATION OF GAS PHASE NUCLEATION IN A NOVELLUS C1 WCVD PROCESS CHAMBER," IEEE/SEMI Advanced Semiconductor Manufacturing Conference, 1995, pgs. 17-22
	AX	Jenny ASBELL, et al., "IMPROVING TUNGSTEN CVD PERFORMANCE WITH IN SITU PARTICLE MONITORING," Micro, July/August 1997, pgs. 63-73
	AY	
	AZ	

Examiner



Date Considered SEP. 30, 2001

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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